

Fundamentals of the Infrared Physical Layer

*Author: Paul Barna
Microchip Technology Inc.
Steve Schlanger
Aegis Technologies LLC*

INTRODUCTION

Infrared light, commonly referred to as “IR”, is a common, easy-to-use, low power and low-cost media to transmit information. Among the few “wireless” communication choices, IR has the significant advantage of compatibility with hundreds of millions of electronic devices with IR ports (i.e., laptop PCs, PDAs).

The vast majority of IR-capable devices are compatible with a set of standards established by the Infrared Data Association, or IrDA®. These standards include guidelines for implementing the IR Physical Layer (IrDA Serial Infrared Physical Layer specification), ensuring that IR communication can be established through free space between two dissimilar devices.

This document describes the fundamentals of the infrared physical layer, the IrDA standard and selecting the proper discrete emitter and photodiode components for circuit implementation.

FUNDAMENTALS

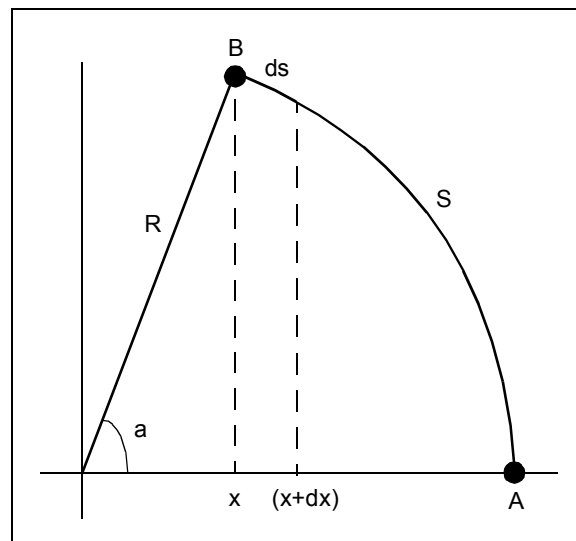
To better understand the design requirements of an IR application, one needs to understand the fundamental behavior of the components.

The Steradian

IR behavior can be predicted more easily than can RF behavior. The devices that emit and detect IR are very simple. The challenge to the designer is to predict how much energy is available from which the information may be extracted. RF designers are familiar with the concept of a “Link Budget”. This simple method starts with how much energy is put into the air and is attenuated by the inverse-square ratio, leaving a minimum signal level for the receiving circuit to detect. The Link Budget for IR is handled in the same way. The unit measure of energy in IR is mW/Sr, with ‘Sr’ being the abbreviation for steradian. Understanding the steradian is key to planning for the energy available in the application.

To understand the steradian, we will first consider the radian. The radian is defined as the angle ‘a’ that produces an arc ‘S’ that is equal in length to the radius ‘R’ and is equal to $360/2\pi$ degrees ($\sim 57^\circ 17' 46.6''$). The arc is created by moving the radius arm from point A to point B at the given angle, as shown in Figure 1. There are 2π radians in a circle.

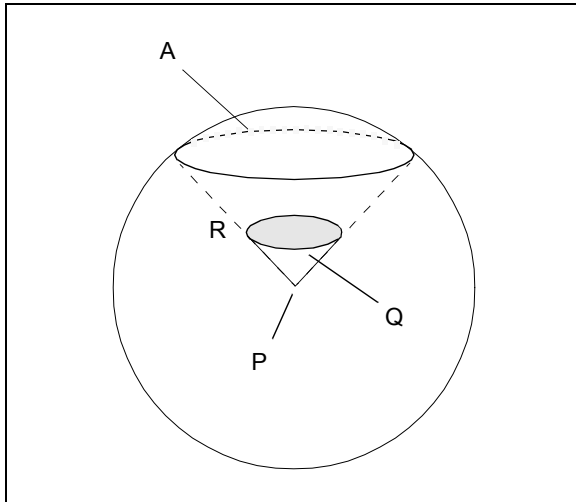
FIGURE 1: ARC DESCRIBED BY A RADIAN



The steradian is defined as conical in shape, and is the Standard International (SI) unit of solid angular measure. It may be examined by rotating the arc ‘S’ (from Figure 1) around the X-axis. The resulting area is a part of the surface of a sphere, as shown in Figure 2, where point ‘P’ represents the center of the sphere.

The solid (conical) angle ‘Q’, representing one steradian, is such that the area ‘A’ of the subtended portion of the sphere is equal to R^2 , where ‘R’ is the radius of the sphere. There are 4π , or approximately 12.57 steradians, in a complete sphere.

FIGURE 2: AREA DESCRIBED BY A STERADIAN



Calculating the exact area swept out by a steradian is much like calculating the area of a sphere. Referring back to Figure 1, the area swept out by rotating arc 'S' around the x-axis may be found as follows:

$$F(x) = \sqrt{(R^2) - (x^2)} \quad \text{Function for the arc}$$

$$f(x) = \left[-\frac{x}{\sqrt{(R^2) - (x^2)}} \right] \quad \text{Derivative of the arc function}$$

$$A = 2\pi \int_x^R F(x) \sqrt{1 + f(x)^2} dx \quad \text{Area formed by 'S', starting from x and going to 'R'}$$

$$A = 2\pi \int_{R \cos(a)}^R R dx \quad \text{Simplify and replace 'x' with 'R' times cos(a)}$$

While Equation 1 is given in the IrDA standard documentation, the above derivation is not. This form is important because the "half-angle", as shown by angle 'a' in Figure 1, is usually given by the emitter and detector manufacturers.

EQUATION 1: AREA FUNCTION GIVEN ANGLE 'a'

$$A = 2\pi R^2 (1 - \cos(a))$$

The number of steradians in a given solid angle can be determined by dividing the area on the surface of the sphere lying within the intersection of the solid angle by the square of the radius of the sphere, as indicated in Equation 2.

EQUATION 2: STERADIAN AS A FUNCTION OF AREA AND RADIUS OF A SPHERE

$$Sr = \frac{A}{R^2} \quad \text{Steradian definition}$$

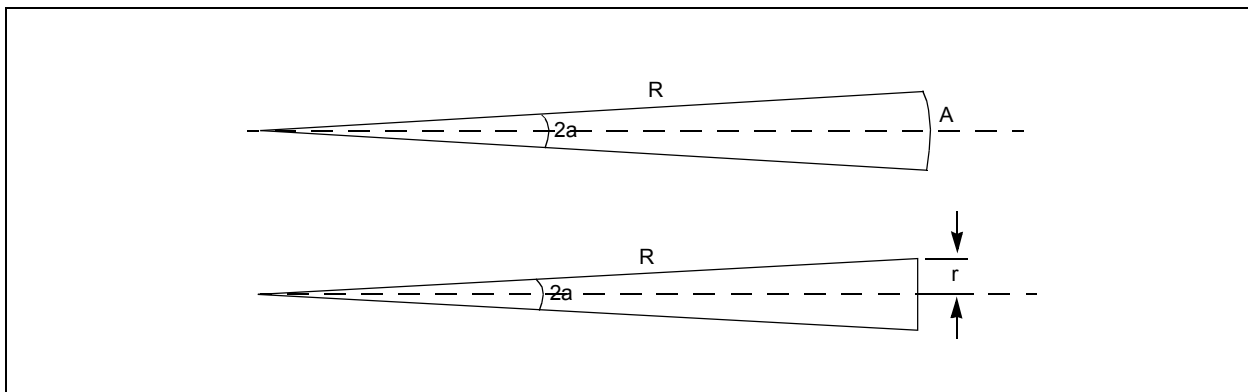
At relatively long distances from the emitter, the curved surface area, defined by 'A', can be replaced by the area of a flat circle, as indicated in Figure 3 and Equation 3.

EQUATION 3: STERADIAN APPROXIMATION

$$Sr = \frac{\pi r^2}{R^2} \quad \text{use a relatively long distance from emitter}$$

We now have the tools to calculate the area the emitted light of a point source (Light Emitting Diode) is spread over, at both short and long distances.

FIGURE 3: FLAT CIRCLE APPROXIMATES SEGMENT OF SPHERE



Let's consider a case where the radius of a sphere is 1 meter and $a = 15^\circ$ (the minimum half-angle for emitters and detectors, as defined by the IrDA Physical Layer specification). How is $\pm 15^\circ$ converted to steradians? To begin with, calculate the area of the sphere that is intersected by the solid angle:

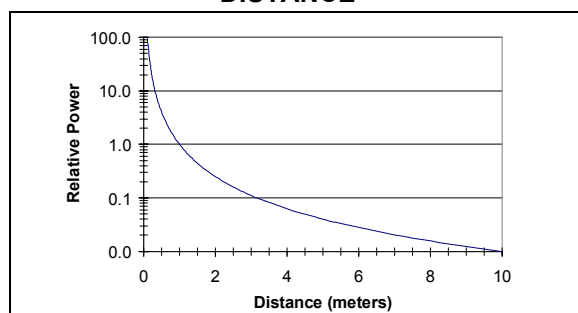
$$\begin{aligned}
 R &= 1 \text{ meter} && \text{Radius of the sphere} \\
 a &= \frac{(15)}{180}\pi && \text{Convert the angle to radians} \\
 A &= 2\pi R^2(1 - \cos(a)) \\
 A &= 0.214 \text{ meters} && \text{Projected area of solid angle}
 \end{aligned}$$

Finally, from Equation 2, the number of steradians is calculated by dividing the area, A, by the square of the radius, R. Therefore, 0.214 steradians translates to an area of 0.214 m² when the radius is 1 meter and the half-angle is 15° (by definition, the number of steradians is equal to the projected area on a unit sphere).

Steradians and Light Energy

If the radius were increased to 2, 'A' would increase by a factor of 4 (while maintaining the same half-angle). This distance-square function of the area is the reason the available power drops as a function of the square of the distance. The *total* power projected on the larger area is the same, though the area that the power is distributed across increases. This relationship is illustrated in Figure 4.

FIGURE 4: POWER AS A FUNCTION OF DISTANCE



Other Units

Modern IR emitters used for data communication are usually specified in mW/Sr. Another unit sometimes used is millicandela (mcd). Visible LEDs are commonly specified in mcd. One candela is also the same as one Lumen/Sr. The candela is a unit of luminous flux, defined by the General Conference of Weights and Measures (CGPM).

The definition of the candela is the luminous intensity, in a given direction, from a source that emits a specified monochromatic radiation. There are actually two parts to this definition, the *intensity* and the *wavelength*.

The radiant *intensity* of the source is specified at 1/683 W/Sr, or 1.46 mW/Sr. One mcd is, therefore, equal to 1.46E-3 mW/Sr. However, it should be noted that the radiant intensity of an emitter is dependent on the angle at which the light source is measured. This is discussed in more detail in the next section.

The *frequency* of the source is specified at 540e12 Hz, or a wavelength of 555 nm (this light is green in color and is very close to the peak sensitivity of the human eye). When a calibrated photo detector is used, the calibration is established at a narrow wavelength. This part of the definition indicates the wavelength of this calibration, but the definition may be used at any wavelength.

THE IR LIGHT EMITTER

There are many off-the-shelf, commercially available, IR LED emitters that can be used for a discrete infrared transceiver circuit design. It should be mentioned here that there are also a number of integrated transceivers that the designer can choose as well. However, designing a discrete transceiver yourself may yield significant gains in distance, power consumption, lower cost or all the above.

In general, there are four characteristics of IR emitters that designers have to be wary of:

- Rise and Fall Time
- Emitter Wavelength
- Emitter Power
- Emitter Half-angle

The IrDA Physical Layer specification provides guidance for a given active output interface at various data rates, both in "Low-power" and "Standard" configurations. Table 1 summarizes the primary specifications in the low-power configuration (20 cm in distance) at data rates up to 115.2 kbps.

TABLE 1: IrDA STANDARD LOW-POWER ACTIVE OUTPUT SPECIFICATION

Specification	Min.	Max.	Units
Peak Wavelength	850	900	nM
Intensity in Angular Range (Emitter Power)	3.6	72	mW/Sr
Half Angle	15	30	Degrees
Rise and Fall Time	—	600	nsec

Table 2 summarizes the primary specifications in the standard configuration (up to 1 meter in distance) at data rates up to 115.2 kbps.

TABLE 2: IrDA STANDARD ACTIVE OUTPUT SPECIFICATION

Specification	Min.	Max.	Units
Peak Wavelength	850	900	nM
Intensity in Angular Range (Emitter Power)	40	500	mW/Sr
Half Angle	15	30	Degrees
Rise and Fall Time	—	600	nsec

The designer may desire to modify these requirements based on the particulars of the application. For example, an application may be required to communicate over a greater distance than 1 meter. In this case, the required light intensity may need to be greater than the stated maximum intensity specified by the IrDA specification.

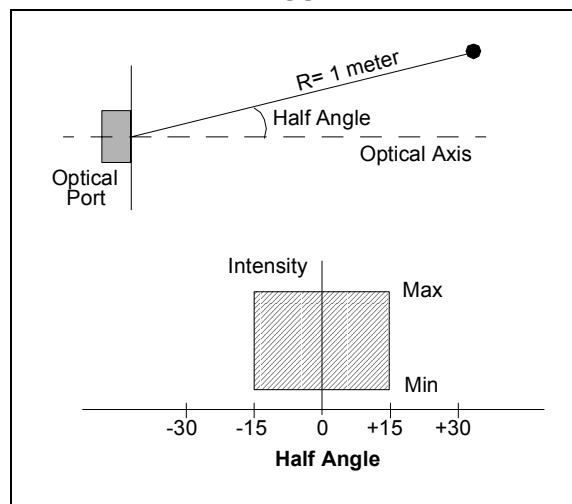
The first, and most important, emitter specification is its switching speed, expressed as t_{on}/t_{off} in most data sheets. Although the IrDA standard allows t_{on} to take up to 600 ns, the authors have had more consistent results when t_{on} is not more than 100 ns. Emitters used for TV Remote (TVR) applications may have t_{on}/t_{off} times of several microseconds and are not suitable for IrDA applications. If t_{on} or t_{off} are not specified, it can be measured with an oscilloscope. The rise (or fall) time of the current will equal the rise (or fall) time of the light pulse.

The emitter wavelength is usually given as the wavelength that the peak emission, or intensity, occurs. The intensity of larger or smaller wavelengths will fall off as they get farther away from the peak. The IrDA specification defines a range of light frequency that a compatible system will operate at. IR emitters that fall just outside this range may also be considered, but the relative radiant power at the desired wavelength (between 850 to 900 nm) may need to be determined.

To select an appropriate IR Light Emitting Diode (LED), the designer must also consider the emitter power in terms of the light to be made available at a desired distance of communication, as well as the amount of current required to generate the desired light energy.

The amount of light energy, or intensity, is given in mW/Sr and is measured at 1 meter. It is also specified that this intensity will be present over the angular range of the receiver, which is given as 15° (min). This is important because the light from a typical LED is not evenly distributed. Figure 5 illustrates the relationship of angular angle to the emitting diode, and light intensity requirements of the IrDA standard at the minimum angular range of 15°.

FIGURE 5: OPTICAL PORT ANGLE MEASUREMENT



Analysis of an IR LED

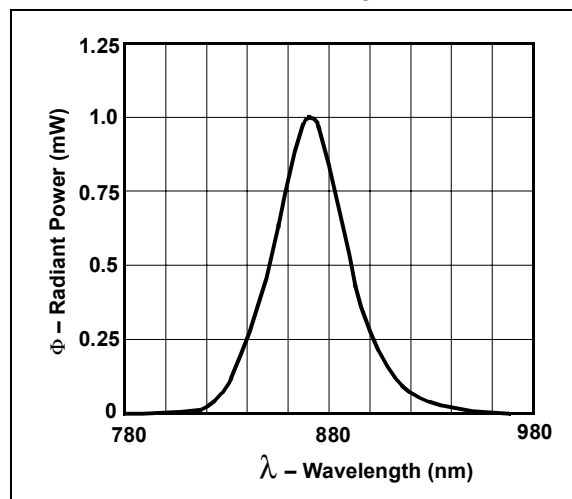
Let us now consider an actual IR LED, the Vishay™ TSHF5400, to determine if it will meet these guidelines.

EXAMPLE 1: IR LED ANALYSIS

Emitter Type:	TSHF5400
Emitter Pulse Current:	300 ma
Angular Displacement:	0 Degrees
Link Distance:	1 m

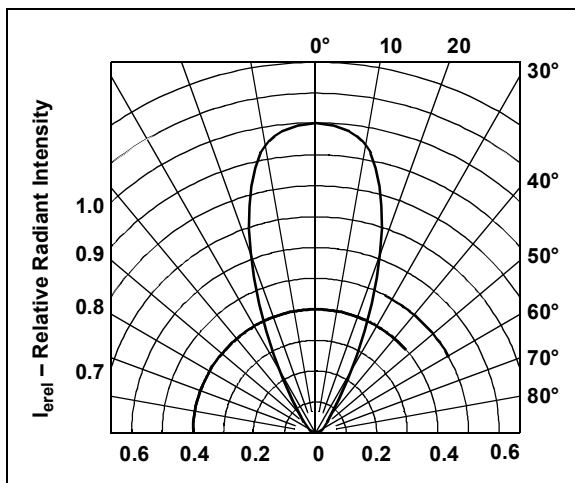
The peak wavelength for this LED is 870 nm. Figure 6 shows a graph of the Radiant Power (mW) versus Wavelength (nm).

FIGURE 6: RADIANT POWER VS. WAVELENGTH



As previously mentioned, the amount of light from a light-emitting diode is not evenly distributed. Figure 7 is a graph of the Relative Radiant Intensity (i.e., Emitted Power) versus Angular Displacement for a Vishay TSHF5400 IR emitter.

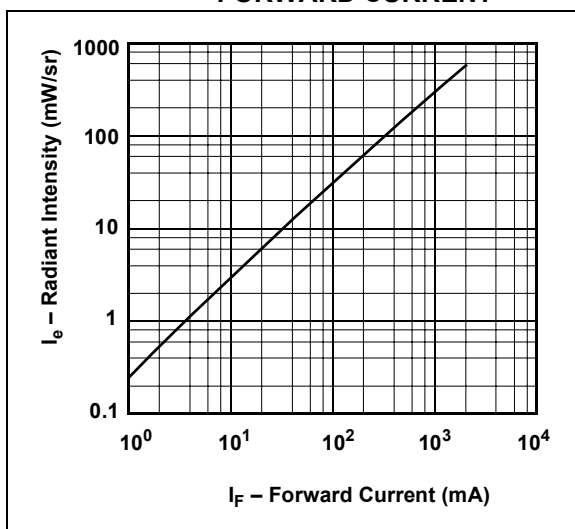
FIGURE 7: NORMALIZED INTENSITY VS. ANGULAR DISPLACEMENT



Since this graph is “normalized” (the relative strength is shown versus the angle at which the light is measured), the rated output is only available at an angle of 0°. At an angle of 15°, the output drops to 80% of the rated output.

Finally, the graph illustrated in Figure 8 indicates the radiant intensity that can be expected when the LED is provided a forward current.

FIGURE 8: RADIANT INTENSITY VS. FORWARD CURRENT



For this example, let's say the LED driver in the application can provide an emitter current pulse of 300 mA. So how much light can be expected?

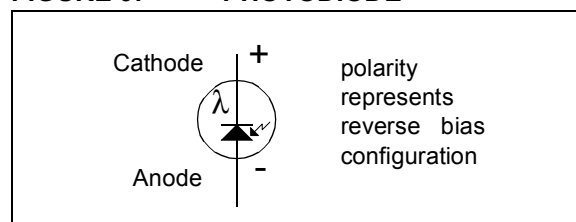
The graph shown in Figure 8 indicates that, for a current of 300 mA, the light intensity is about 100 mW/Sr., with a relative radiant intensity of 80% at an angle of 15° (indicated in Figure 7). Therefore, a minimum intensity of 80 mW/Sr can be expected at a distance of 1 meter within the angular range of 15° (the minimum half-angle specified by the IrDA standard).

Note: The IR emitter and detectors may be on a Printed Circuit Board (PCB) that is within an enclosure behind a plastic window. An additional loss may be incurred, depending on the type of material and its thickness. For this example, no loss is assumed. In practice, most types of plastic with a thickness of 1.5 mm will lose about 10%. The same thickness of glass will lose 2-3%.

THE IR LIGHT DETECTOR

The most common device used for detecting light energy in the IrDA standard data stream is a photodiode. Integrated IrDA standard transceivers use a photodiode as the receiver, while TVR applications commonly use a photo transistor. Photo transistors are not typically used in IrDA standard-compatible systems because of their slow speed. Photo transistors typically have t_{on}/t_{off} of 2 μ s or more. A photo transistor may be used, however, if the data rate is limited to 9.6 kb with a pulse width of 19.5 μ s. Figure 9 shows a common symbol for a photodiode.

FIGURE 9: PHOTODIODE



A photodiode is similar in many ways to a standard diode, with the exception of its packaging. A photodiode is packaged in such a way as to allow light to strike the PN junction. In infrared applications, it is common practice to apply a reverse bias to the device. Refer to Figure 12 for a characteristic curve of a reverse biased photodiode. There will be a reverse current that will vary with the light level. Like all diodes, there is an intrinsic capacitance that varies with the reverse bias voltage. This capacitance is an important factor in speed.

Another operating mode occurs near the device breakdown voltage. Near breakdown, the velocity of minority charge carriers crossing the junction is increased. These high-energy charge carriers strike atoms in the depletion region, causing a large number of charge carriers to be knocked out of these atoms, causing a chain reaction of avalanche current. Light striking the junction will enhance this effect. Operating in the avalanche mode involves applying a constant current power supply to the reverse biased photodiode. This power supply must have a sufficiently high voltage to reach the device breakdown voltage. When light strikes the junction, the voltage needed by the power supply to maintain the constant current will be reduced. This method offers both high-speed and very high sensitivity. The disadvantage is both high cost and high-power consumption. This method is seldom used outside of military applications.

Link Distance

To select an appropriate IR photo-detect diode, the designer must keep in mind the distance of communication, the amount of light that may be expected at that distance and the current that will be generated by the photodiode given a certain amount of light energy.

The IrDA Physical Layer specification provides guidance for a given active-input interface at various data rates, in low-power and standard configurations. Table 3 summarizes the primary specifications in the low-power configuration (up to 20 cm in distance) at data rates up to 115.2 kb/s.

TABLE 3: IrDA STANDARD LOW POWER ACTIVE INPUT SPECIFICATION

Specification	Min.	Max.	Units
Irradiance in Angular Range	9	5x10 ⁵	μW/cm ²
Half Angle	15	—	Degrees
Receiver Latency	—	0.5	msec

Table 4 summarizes the primary specifications in the standard configuration (up to 1 m in distance) at data rates up to 115.2 kb/s.

TABLE 4: IrDA STANDARD ACTIVE-INPUT SPECIFICATION

Specification	Min.	Max.	Units
Irradiance in Angular Range	4	5x10 ⁵	μW/cm ²
Half Angle	15	—	Degrees
Receiver Latency	—	10	msec

As with the IR LED, the designer may wish to modify these design guidelines based on the particulars of the application.

The amount of light energy, or irradiance, that is present at the active-input interface is typically given in μW/cm². This is a convenient scale of light flux. Light energy given in mW/Sr can be converted to μW/cm² as follows. Recall from Equation 2 that:

$$Sr = \frac{A}{R^2}$$

To convert Sr to cm², the distance must be known. In this example, R = 1 meter. The area of the circle of interest can be set to one square centimeter (0.0001 m²). So, at a distance of 1 meter, the area of 1 steradian is equal to 1 square meter (or 10,000 cm²). It follows that 40 mW/Sr is equal to 4 μW/cm², the minimum irradiance requirement of the IrDA standard configuration active input.

It is also specified that this irradiance must be present over a minimum angular range of the receiver, which is given as 15°.

It is interesting to note that at a distance of 2 feet, or 0.6 meters, an IrDA standard-compliant emitter will provide 2.8X the light intensity that is available at 1 meter, based on the distance-squared function stated in Equation 2 and illustrated in Figure 4.

The latency of the input interface must be less than 10 msec.

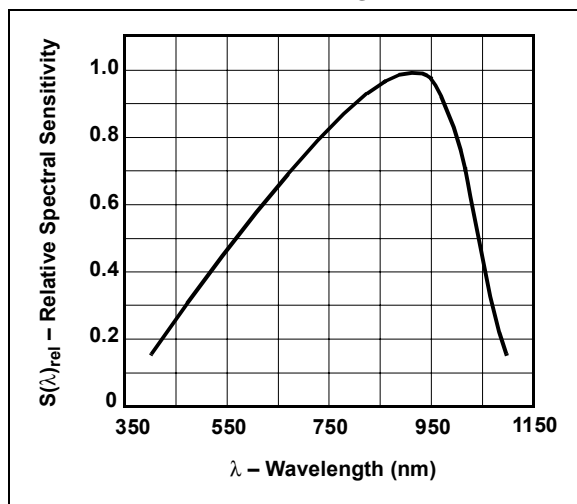
Analysis of a Photo-Detect Diode

Let us now consider an actual IR photo-detect diode, the Vishay BPV10, to determine if it will meet these guidelines.

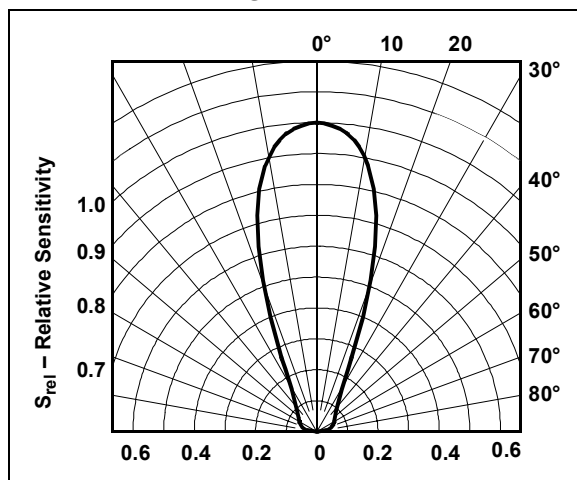
EXAMPLE 2: PHOTO DIODE ANALYSIS

Receiver Type:	BPV10
Angular Displacement:	15 Degrees
Link Distance:	1 m

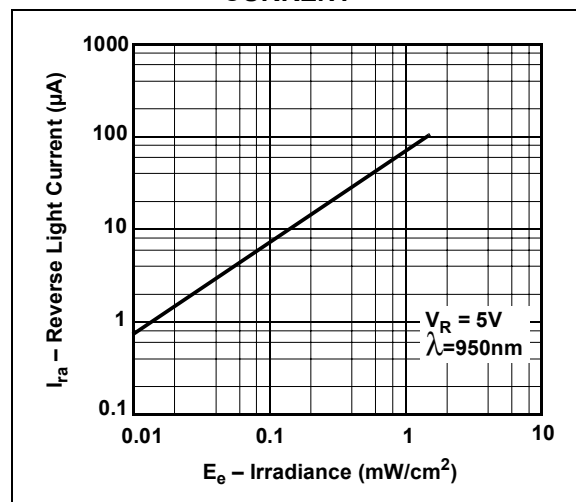
The peak wavelength for this diode is 950 nm. Figure 10 shows a graph of the Relative Spectral Sensitivity versus Wavelength (nm).

FIGURE 10: SENSITIVITY VS. WAVELENGTH

The light sensitivity of a photo-detect diode varies according to the angle of the light source. Figure 11 is a graph of the Relative Radiant Sensitivity versus Angular Displacement for a Vishay BPV10 photo-detect diode. At a half-angle of 15° , a relative sensitivity of 75% can be expected.

FIGURE 11: NORMALIZED SENSITIVITY VS. ANGULAR DISPLACEMENT

Finally, the graph illustrated in Figure 12 indicates the reverse current that can be expected when the Photodiode is subjected to a light irradiance.

FIGURE 12: IRRADIANCE VS. CURRENT

The reverse light current goes up with increasing levels of irradiance, as expected. The reverse current is also roughly linear to the irradiance. That is, if the light irradiance is reduced by a factor of 10, the reverse light current is also reduced by a factor of 10. The irradiance is scaled in mW/cm^2 . Extrapolating the graph in Figure 12 indicates that a light pulse of $0.004 \text{ mW}/\text{cm}^2$ ($40 \text{ mW}/\text{Sr}$) will generate a reverse current level around $0.33 \mu\text{A}$. Noting that the relative sensitivity at a half-angle of 15° is 75% per Figure 11, a current pulse of about $0.25 \mu\text{A}$ could be expected at this half-angle.

Recall that light energy (intensity) increases exponentially with respect to distance (Figure 4). At a distance of 2 feet, or 0.6 meters, the amount of energy and, therefore, the reverse current, is roughly 2.8X the energy present at 1 meter. In this example, a current pulse of $0.7 \mu\text{A}$ could be expected at 2 feet at a half-angle of 15° . If larger distances are required, a photo-detect diode with higher sensitivity may be required. Another alternative is to use two or more diodes in parallel to generate more current at low light energies.

In general, the cost of the photo-detect diode will increase with increased performance. A diode with a larger photo-sensitive area can be selected to provide a higher current output, but this will increase the overall cost of the discrete transceiver circuit. The distance requirement of the application should be clearly defined at the outset of the design, allowing the system designer to provide an adequate and cost-effective solution.

INCREASING THE LINK DISTANCE

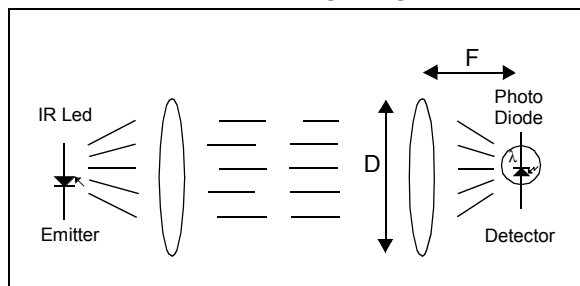
Finally, more than one meter may be required for IR communication in some applications, even though the physical layer of the IrDA standard configuration is built around this distance. Let's take an example where an application needs to communicate with a standard device, like a Palm™ PDA, at an extended distance. Since the power emitted by the Palm IR driver is fixed, one approach would be to ensure that the sensitivity of the receiver is sufficient to support the available light intensity. Increasing this sensitivity by a factor of 4 would only double the distance to 2 meters. The receiver cost and complexity will therefore increase much faster than the increase in distance. As mentioned in the previous section, two or more photo-detect diodes can be connected in parallel to achieve a higher current output. Such an increase in sensitivity takes care of one-half of the link, but data must be sent back to the Palm PDA as well.

Increasing the emitter power by a factor of 4 would also increase the link distance to 2 meters. This approach has limited potential because the emitter power must be limited for eye safety reasons. The pupil of the human eye will not react to IR light and the instinct to look away is not triggered. A single-point IR source of greater than 200 mW/Sr at 1 meter should be avoided for this reason.

Multiple emitters can be used to circumvent this problem. 4 meter IrDA standard links have been designed by using 16 IrDA standard-compliant emitters. Of course, using such a large number of emitters has obvious trade-offs in cost, power and complexity.

Another approach involves using lenses. Figure 13 shows a possible combination of lenses. Lenses have no moving parts and may be fabricated from inexpensive plastics. Plastic lenses are not common for visual applications due to the fact that loss and spectral distortion occurrences are higher than with glass. With infrared applications, we're only interested in a single wavelength of light so spectral distortion is not a factor. Loss is also not a factor because multiple lenses will not be used.

FIGURE 13: USING A LENS TO INCREASE DISTANCE



In practice, it's more common to be compatible with a standard device (e.g., Palm PDA), so one lens on the photo-diode (detector) side will suffice. If compatibility with a standard device is not an issue, links on the order of tens of meters can easily be achieved by implementing lenses on both sides.

An application using Optical Lenses

What lens specification would be needed to establish an IR link at a distance of 5 meters? Assume an emitter power of 200 mW/Sr, a minimum threshold irradiance requirement of 0.02 mW/cm² and a half-power angle of ±15°.

The two specifications of interest in this lens are the focal length and diameter. The amount of energy gathered by the lens is a function of the diameter. As we calculated earlier, an area of 1 cm² at a distance of 1 meter is a solid angle of 1 x 10⁻⁴ Sr. The calculation we performed earlier is as follows:

$$200 \frac{mW}{Sr} \times 10^{-4} \frac{Sr}{cm^2} = 0.02 \frac{mW}{cm^2}$$

To keep the same level of light flux, we need to keep the same solid angle (1 x 10⁻⁴ Sr) and determine the projected area at 5 meters.

EXAMPLE 3: CALCULATING THE RADIUS OF THE LENS (r)

$$Sr = \frac{\pi r^2}{R^2} \quad \text{We know the angle and R is given as 5 meters. The radius of the lens is r}$$

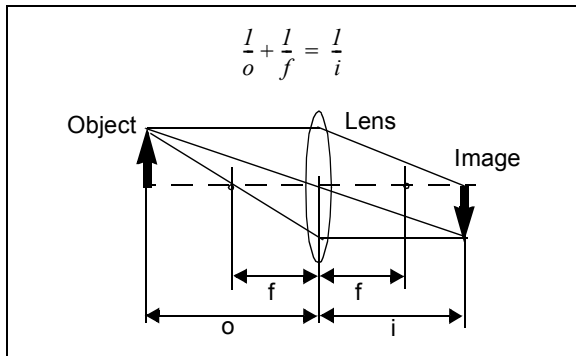
$$R = 5 \text{ m} \quad Sr = 1 \times 10^{-4}$$

$$r = \sqrt{\frac{Sr \cdot R^2}{\pi}} \quad r = 0.028 \text{ meters} \quad \text{Rearrange and solve for r}$$

The radius of the lens must therefore be 2.8 cm (a diameter of 5.6 cm) in order to capture the same level of light flux that was available within a 1 cm² area at a distance of 1 meter.

Next, we need to determine the distance between the lens and the photodiode. The Thin Lens equation, in Gaussian form, is given in Equation 4, where 'o' is the object distance, 'f' is the focal distance and 'i' is the image distance.

EQUATION 4: THIN LENS EQUATION

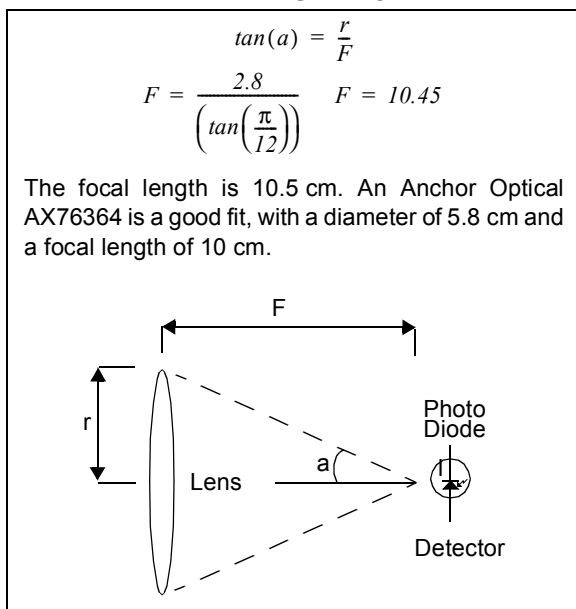


For most applications, 1/object distance is approximately zero. Therefore, the focal length and diameter are the two specifications needed to select the lens.

There are several factors to consider when specifying the focal length, including ease of packaging, depth of field and the amount of energy to capture. A longer focal length will make the lens easier to focus (larger depth of field) but will make the application physically larger.

Let's assume that the half-power angle, which is also the angle of half-sensitivity, will subtend the outer edge of the lens. In this case, the lens radius 'r' is 2.8 cm and the angle 'a' is given as 15°. The focal length calculation is shown in Equation 5.

EQUATION 5: FOCAL LENGTH CALCULATION



CONCLUSION

Whether designing to the IrDA standard or developing a custom interface, the fundamentals of the infrared physical layer are straightforward, since the behavior of IR is easy to predict.

The system designer can use an integrated transceiver or select low-cost, off-the-shelf components to implement an effective IR port, once the Link Budget and application requirements are understood.

REFERENCES

1. Infrared Data Association Serial Infrared Physical Layer Specification, Version 1.4, May, 2001.
2. "High Speed IR Emitting Diode in ϕ 5 mm (T-1 $\frac{3}{4}$) Package", TSHF5400 Data Sheet, Vishay Semiconductors, 1999.
3. "Silicon PIN Photodiode", BPV10 Data Sheet, Vishay Semiconductors, 1999.

NOTES:

Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products. Attempts to break microchip's code protection feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue for relief under that Act.

Information contained in this publication regarding device applications and the like is intended through suggestion only and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. No representation or warranty is given and no liability is assumed by Microchip Technology Incorporated with respect to the accuracy or use of such information, or infringement of patents or other intellectual property rights arising from such use or otherwise. Use of Microchip's products as critical components in life support systems is not authorized except with express written approval by Microchip. No licenses are conveyed, implicitly or otherwise, under any intellectual property rights.

Trademarks

The Microchip name and logo, the Microchip logo, Accuron, dsPIC, KEELOQ, MPLAB, PIC, PICmicro, PICSTART, PRO MATE and PowerSmart are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

Amplab, FilterLab, microID, MXDEV, MXLAB, PICMASTER, SEEVAL, SmartShunt and The Embedded Control Solutions Company are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Application Maestro, dsPICDEM, dsPICDEM.net, dsPICworks, ECAN, ECONOMONITOR, FanSense, FlexROM, fuzzyLAB, In-Circuit Serial Programming, ICSP, ICEPIC, microPort, Migratable Memory, MPASM, MPLIB, MPLINK, MPSIM, PICKit, PICDEM, PICDEM.net, PICtail, PowerCal, PowerInfo, PowerMate, PowerTool, rLAB, rPIC, Select Mode, SmartSensor, SmartTel and Total Endurance are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

Serialized Quick Turn Programming (SQTP) is a service mark of Microchip Technology Incorporated in the U.S.A.

All other trademarks mentioned herein are property of their respective companies.

© 2004, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.

 Printed on recycled paper.

QUALITY MANAGEMENT SYSTEM
CERTIFIED BY DNV
== ISO/TS 16949:2002 ==

Microchip received ISO/TS-16949:2002 quality system certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona and Mountain View, California in October 2003. The Company's quality system processes and procedures are for its PICmicro® 8-bit MCUs, KEELOQ® code hopping devices, Serial EEPROMs, microperipherals, non-volatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.



WORLDWIDE SALES AND SERVICE

AMERICAS

Corporate Office

2355 West Chandler Blvd.
Chandler, AZ 85224-6199
Tel: 480-792-7200
Fax: 480-792-7277
Technical Support: 480-792-7627
Web Address: <http://www.microchip.com>

Atlanta

3780 Mansell Road, Suite 130
Alpharetta, GA 30022
Tel: 770-640-0034
Fax: 770-640-0307

Boston

2 Lan Drive, Suite 120
Westford, MA 01886
Tel: 978-692-3848
Fax: 978-692-3821

Chicago

333 Pierce Road, Suite 180
Itasca, IL 60143
Tel: 630-285-0071
Fax: 630-285-0075

Dallas

4570 Westgrove Drive, Suite 160
Addison, TX 75001
Tel: 972-818-7423
Fax: 972-818-2924

Detroit

Tri-Atria Office Building
32255 Northwestern Highway, Suite 190
Farmington Hills, MI 48334
Tel: 248-538-2250
Fax: 248-538-2260

Kokomo

2767 S. Albright Road
Kokomo, IN 46902
Tel: 765-864-8360
Fax: 765-864-8387

Los Angeles

18201 Von Karman, Suite 1090
Irvine, CA 92612
Tel: 949-263-1888
Fax: 949-263-1338

Phoenix

2355 West Chandler Blvd.
Chandler, AZ 85224-6199
Tel: 480-792-7966
Fax: 480-792-4338

San Jose

1300 Terra Bella Avenue
Mountain View, CA 94043
Tel: 650-215-1444

Toronto

6285 Northam Drive, Suite 108
Mississauga, Ontario L4V 1X5, Canada
Tel: 905-673-0699
Fax: 905-673-6509

ASIA/PACIFIC

Australia

Suite 22, 41 Rawson Street
Epping 2121, NSW
Australia
Tel: 61-2-9868-6733
Fax: 61-2-9868-6755

China - Beijing

Unit 706B
Wan Tai Bei Hai Bldg.
No. 6 Chaoyangmen Bei Str.
Beijing, 100027, China
Tel: 86-10-85282100
Fax: 86-10-85282104

China - Chengdu

Rm. 2401-2402, 24th Floor,
Ming Xing Financial Tower
No. 88 TIDU Street
Chengdu 610016, China
Tel: 86-28-86766200
Fax: 86-28-86766599

China - Fuzhou

Unit 28F, World Trade Plaza
No. 71 Wusi Road
Fuzhou 350001, China
Tel: 86-591-7503506
Fax: 86-591-7503521

China - Hong Kong SAR

Unit 901-6, Tower 2, Metroplaza
223 Hing Fong Road
Kwai Fong, N.T., Hong Kong
Tel: 852-2401-1200
Fax: 852-2401-3431

China - Shanghai

Room 701, Bldg. B
Far East International Plaza
No. 317 Xian Xia Road
Shanghai, 200051
Tel: 86-21-6275-5700
Fax: 86-21-6275-5060

China - Shenzhen

Rm. 1812, 18/F, Building A, United Plaza
No. 5022 Binhe Road, Futian District
Shenzhen 518033, China
Tel: 86-755-82901380
Fax: 86-755-8295-1393

China - Shunde

Room 401, Hongjian Building
No. 2 Fengxiangnan Road, Ronggui Town
Shunde City, Guangdong 528303, China
Tel: 86-765-8395507 Fax: 86-765-8395571

China - Qingdao

Rm. B505A, Fullhope Plaza,
No. 12 Hong Kong Central Rd.
Qingdao 266071, China
Tel: 86-532-5027355 Fax: 86-532-5027205

India

Divyasree Chambers
1 Floor, Wing A (A3/A4)
No. 11, O'Shaughnessey Road
Bangalore, 560 025, India
Tel: 91-80-2290061 Fax: 91-80-2290062

Japan

Benex S-1 6F
3-18-20, Shinyokohama
Kohoku-Ku, Yokohama-shi
Kanagawa, 222-0033, Japan
Tel: 81-45-471-6166 Fax: 81-45-471-6122

Korea

168-1, Youngbo Bldg. 3 Floor
Samsung-Dong, Kangnam-Ku
Seoul, Korea 135-882
Tel: 82-2-554-7200 Fax: 82-2-558-5932 or
82-2-558-5934

Singapore

200 Middle Road
#07-02 Prime Centre
Singapore, 188980
Tel: 65-6334-8870 Fax: 65-6334-8850

Taiwan

Kaohsiung Branch
30F - 1 No. 8
Min Chuan 2nd Road
Kaohsiung 806, Taiwan
Tel: 886-7-536-4818
Fax: 886-7-536-4803

Taiwan

Taiwan Branch
11F-3, No. 207
Tung Hua North Road
Taipei, 105, Taiwan
Tel: 886-2-2717-7175 Fax: 886-2-2545-0139

EUROPE

Austria

Durisolstrasse 2
A-4600 Wels
Austria
Tel: 43-7242-2244-399
Fax: 43-7242-2244-393

Denmark

Regus Business Centre
Lautrup høj 1-3
Ballerup DK-2750 Denmark
Tel: 45-4420-9895 Fax: 45-4420-9910

France

Parc d'Activite du Moulin de Massy
43 Rue du Saule Trapu
Batiment A - 1er Etage
91300 Massy, France
Tel: 33-1-69-53-63-20
Fax: 33-1-69-30-90-79

Germany

Steinheilstrasse 10
D-85737 Ismaning, Germany
Tel: 49-89-627-144-0
Fax: 49-89-627-144-44

Italy

Via Quasimodo, 12
20025 Legnano (MI)
Milan, Italy
Tel: 39-0331-742611
Fax: 39-0331-466781

Netherlands

P. A. De Biesbosch 14
NL-5152 SC Drunen, Netherlands
Tel: 31-416-690399
Fax: 31-416-690340

United Kingdom

505 Eskdale Road
Wokingham
Berkshire, England RG41 5TU
Tel: 44-118-921-5869
Fax: 44-118-921-5820

11/24/03